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HEMT available for less than 72 cents a watt for peak power...

NITRONEX'S 100W GaN ON Si RF POWER TRANSISTOR ENTERS VOLUME PRODUCTION

Durham, N.C. (August 15, 2007) — Nitronex, an innovative developer and manufacturer of high-performance RF power transistors for the commercial and broadband wireless infrastructure markets, has developed a 28V, 100W class gallium nitride on silicon high electron mobility transistor (HEMT) specifically designed for applications operating between 2.1 - 2.7GHz. Designed using Nitronex's patented SIGANTIC® NRF1 process, the production qualified NPT25100 GaN on Si RF power transistor is ideal for continuous wave (CW), pulsed, WiMAX, W-CDMA and long term evolution (LTE) applications. Nitronex's NPT25100 product qualification document is available at <http://www.nitronex.com/wimaxgan/wimaxgan.html>

“We have extended the operating frequency and increased the power output of the NPT25100 devices, while reducing the cost per watt for peak power to the lowest in the GaN industry. The inherent broadband nature of this device combined with its efficient linear power and competitive price point make it a compelling solution for many WiMAX infrastructure applications,” said Ray Crampton, Director of Marketing at Nitronex. “After rigorous testing, the NPT25100 power transistors are production ready and our qualification report is available online.”

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NITRONEX'S 100W GAN ON SI RF POWER TRANSISTOR ENTERS VOLUME PRODUCTION, P. 2

Typical performance using a mobile WiMAX waveform defined as a single carrier OFDM 64-QAM $\frac{3}{4}$, 8 burst, 3.5MHz channel bandwidth, 10.3dB PAR @ .01% probability on CCDF. Under these conditions, the NPT25100 transistor will deliver 16.5dB power gain with a drain efficiency of 26% and an error vector magnitude (EVM) of 2.0% - all at 10W of power. Typical two-tone peak envelope power (PEP) is 125W and drain efficiency is more than 65%.

The NPT25100 transistors are packaged in a thermally enhanced Copper Moly Copper package available in a bolt-down version, with a pill version scheduled to be available in the fourth quarter of 2007. Samples and application boards are now available. Typical pricing is \$90 each in quantities of 1000, with a lead time from stock to eight weeks.

The NPT25100 transistors are lead-free and RoHS compliant.

For more information about Nitronex's NPT25100 GaN on Si RF power transistor, contact Nitronex at 2305 Presidential Drive, Durham, NC 27703; call 919-807-9100; e-mail info@nitronex.com; or visit www.nitronex.com.

About Nitronex

Specializing in the development and manufacturing of gallium nitride (GaN) RF power devices, Nitronex is the global leader in high-performance GaN on silicon (GaN on Si) RF power transistors for the commercial wireless infrastructure, broadband and military markets. Based on its patented SIGANTIC[®] process — gallium nitride on silicon technology — Nitronex is at the forefront of commercializing GaN technology for RF applications. The company's ability to combine the disciplines of material growth, wafer processing, device design and wireless applications knowledge is unique to the industry.

Nitronex was founded in 1999 by graduates of the wide bandgap program at North Carolina State University and is headquartered in Durham, North Carolina. It holds 16 patents with 18 others pending.

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